Form PTO 1449 U.S. DEPARTMENT OF COMMERCE (Modified) PATENT AND TRADEMARK OFFICE			ATTY DOCKET NO.		SERIAL NO. 10/662533		
			242820US2RD	New Application			
LIST OF	OEEEE	PENCES CITED BY AD	DUCANT	APPLICANT			
LIST OF REFERENCES CITED BY APPLICANT				Yoshiaki SAITO, et al.	Taraus		
			FILING DATE		GROUP		
				Herewith			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
ુખ	AA	5,659,499	08/19/97	E. CHEN, et al.	11_		
04	AB	5,956,267	09/21/99	A. T. HURST, et al.			
94	AC	5,734,605	03/31/98	X. T. ZHU, et al.		1	
رجو	AD	5,640,343	06/17/97	W. J. GALLAGHER, et al.			
Del	AE	5,940,319	08/17/99	M. DURLAM, et al.		1 [	
سق	AF	6,351,408	02/26/2002	S. SCHWARZL, et al.	$T^{T}$		
	AG						
	AH						
	Al				1		
	AJ						
	AK				<del> </del>		
	AL		<del> </del>		<del> </del>	<del>                                     </del>	
	AM				<del> </del>		
	AN		<del> </del>		<del> </del>	<del> </del>	
	AIN	L					<u> </u>
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY		TRANSLATION YES NO	
ہیں	AO	WO 00/10172	02/24/2000	WIPO (with English Abstract)			х
Oe4	AP	10-4227	01/06/98	JAPAN (with English Abstract)			Х
<del>y</del>	AQ	WO 99/14760	03/25/99	WIPO (with English Abstract)			X
194	AR	197 44 095	04/15/99	WIPO (with corr. US 6,351,408)			, X
	AS						
	AT						
<del></del>	AU		1			<del>                                     </del>	
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
J. S. MOODERA, et al., "FERROMAGNETIC-INSULATOR-FERROMAGNETIC TUNNELING: SPIN-DEPENDENT TUNNELING AND LARGE MAGNETORESISTANCE IN TRILAYER JUNCTION (INVITED)", Vol. 79, No. 8, pgs. 4724-4729, J. Appl. Phys., April 15, 1996							
Ou	AW	L. F. SCHELP, et al., "SPIN-DEPENDENT TUNNELING WITH COULOMB BLOCKADE", Vol. 56, No. 10, pgs. R5747- R5750, Physical Review B, September 1, 1997					
۳	AX	Y. SAITO, et al., "SPIN-DEPENDENT TUNNELING THROUGH LAYERED HARD-MAGNETIC-NANO-PARTICLES", Vol. 23, No. 4-2, pgs. 1259-1272, J. Jpn. Appl. Magn. Society, 1999 (with English Abstract)					
Ou	AY	F. MONTAIGNE, et al., "ENHANCED TUNNEL MAGNETORESISTANCE AT HIGH BIAS VOLTAGE IN DOUBLE-BARRIER PLANAR JUNCTIONS", Vol. 73, No. 19, pgs. 2829-2831, Applied Physics Letters, November 9, 1998					
Je	AZ	Y. SAITO, et al., "CORRELATION BETWEEN BARRIER WIDTH, BARRIER HEIGHT, AND DC BIAS VOLTAGE DEPENDENCES ON THE MAGNETORESISTANCE RATIO IN Ir-Mn EXCHANGE BIASED SINGLE AND DOUBLE TUNNEL JUNCTIONS", Vol. 39, pgs. L1035-L1038, Jpn. J. Appl. Phys., 2000					
Examiner U. 10					Date Considered 03/07/04		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in							
conformance and not considered. Include copy of this form with next communication to applicant.							